

SOT-23 Plastic-Encapsulate Transistors**BC817-16 BC817-25****BC817-40 TRANSISTOR (NPN)****FEATURES**

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)

SOT-23

1. BASE
2. Emitter
3. Collector

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_c	Collector Current -Continuous	0.5	A
P_c	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN		MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C= 10\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C= 10\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	V_{EBO}	$I_E= 1\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}= 45 \text{ V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= 4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}= 1\text{V}, I_C= 100\text{mA}$	100		600	
	$h_{FE(2)}$	$V_{CE}= 1\text{V}, I_C= 500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C= 500\text{mA}, I_B= 50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C= 500\text{mA}, I_B= 50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}= 1 \text{ V}, I_C= 500\text{mA}$			1.2	V
Collector capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$		10		pF
Transition frequency	f_T	$V_{CE}= 5 \text{ V}, I_C= 10\text{mA}$ $f=100\text{MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	BC817-16	BC817-25	BC817-40
Range	100-250	160-400	250-600
Marking	6A	6B	6C